

# Hydrogen Effects on Dislocation Dynamics and Metal Plasticity

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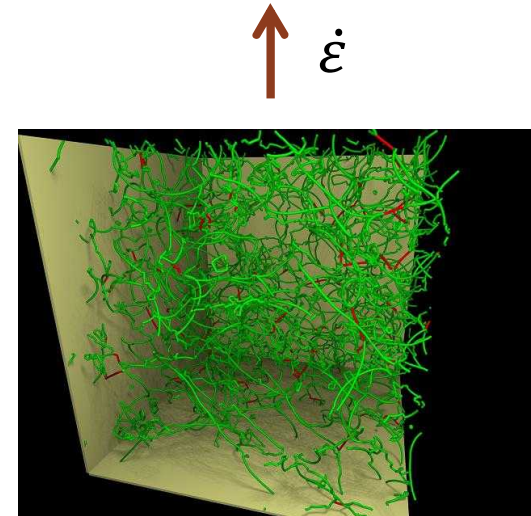
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# Overview

- Dislocation dynamics (DD) primer
- Adding hydrogen effects to DD
- Simulations with hydrogen effects

# Dislocation dynamics

- Simulate motion of dislocation lines in an elastic medium
- Physics controlled (primarily) with:
  - › Driving force calculation
    - Elastic interactions
    - Applied stresses



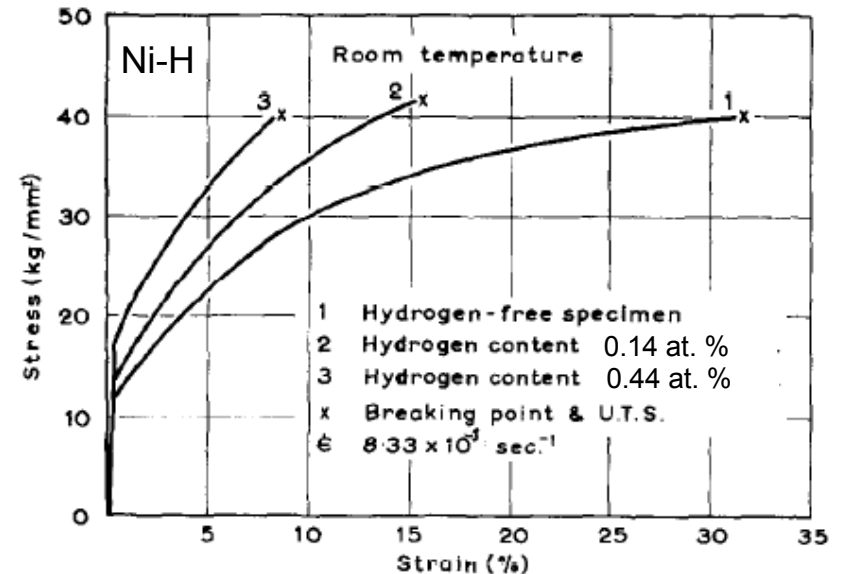
From paradis.stanford.edu

- › Mobility law

$$Bv = f_{el} + f_{app} + \dots$$

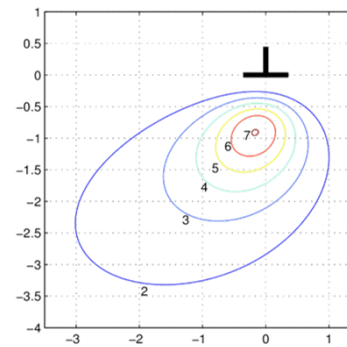
Drag Coefficient

- To date, models primarily developed for *pure metals*



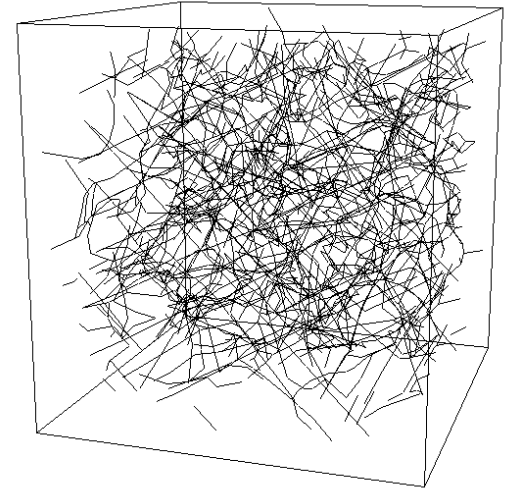
From Boniszewski and Smith, 1963

# Adding H-Effects to Dislocation Dynamics



# Overall approach

- Interested in large-scale work hardening
- Full simulation of hydrogen field infeasible
  - › Large number of lattice sites ( $\sim 1 \times 10^{10} / \mu\text{m}^3$ )
  - › Dislocation stress fields highly nonlinear
    - Very fine computational grid required
- Our approach: Study solute effects on isolated dislocations
  - Use **force calculation** and **mobility law** to incorporate effects



# Solid solution model

- H atoms occupy interstitial lattice sites
  - › Excess volume  $\Delta V$
  - › Dilatational misfit only
  - › No modulus change
- Characterized by concentration field,  $c(\mathbf{r})$
- Chemical potential:

› Free energy cost of a solute

$$\mu = E_f + p_d \Delta V + k_B T \ln \left( \frac{c}{c_{max} - c} \right)$$

Formation Energy
Interaction Energy
Configurational Entropy

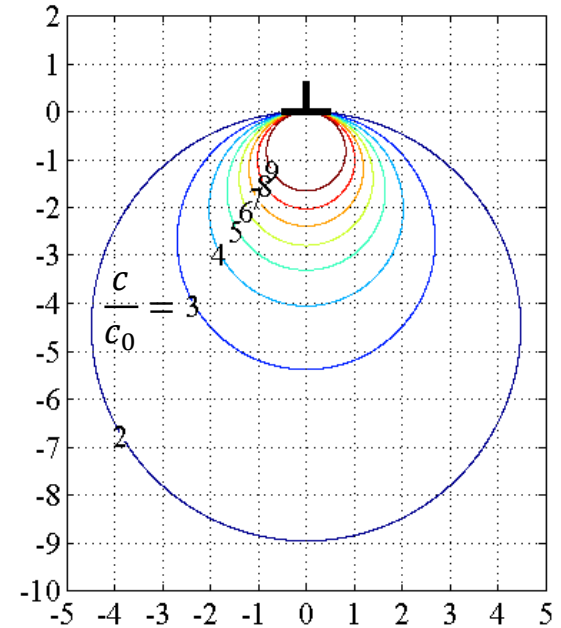
Equilibrium Concentration

$$c = \frac{c_{max}}{1 + \frac{c_{max} - c_0}{c_0} \exp[p_d \Delta V / k_B T]}$$

Diffusion Equation

$$\frac{\partial c}{\partial t} = -\nabla \cdot \mathbf{J}$$

$$\mathbf{J} = -\frac{Dc}{k_B T} \nabla \mu$$



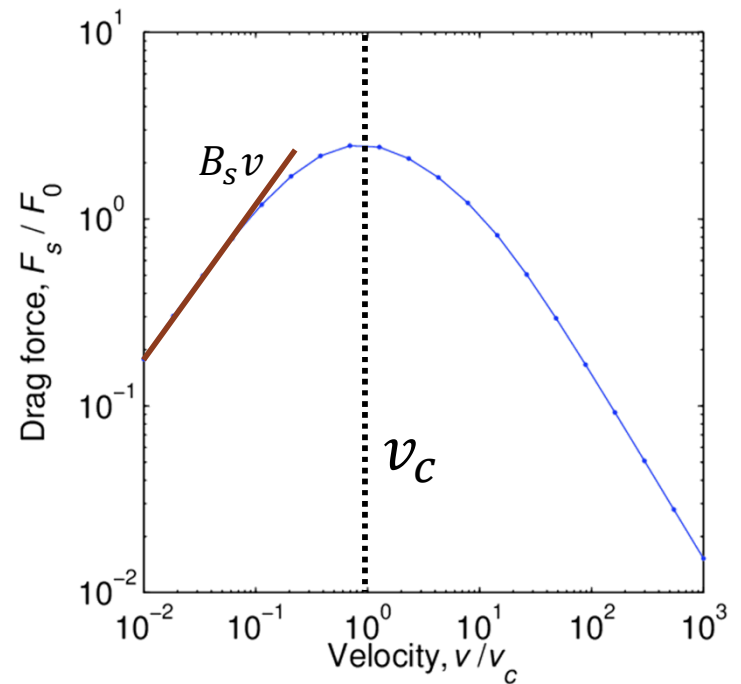
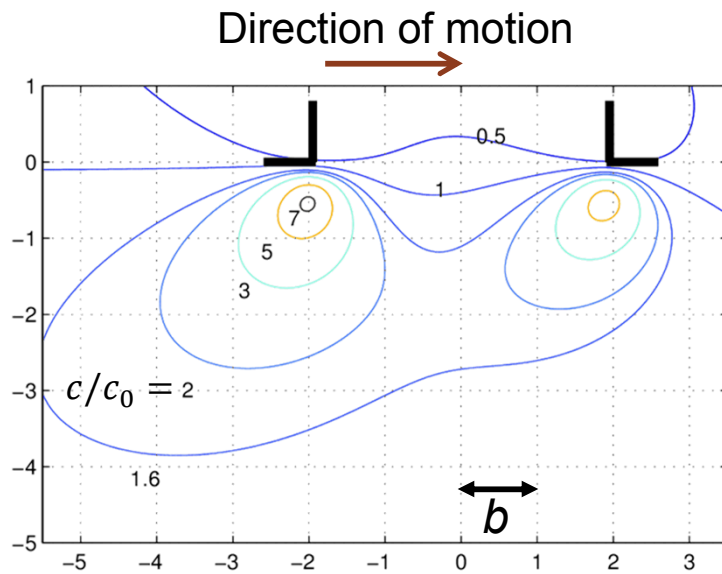
# H effects on dislocations

- Hydrogen (solutes) affect dislocations on multiple ways

Effect	Force Calculation	Mobility Law	Other
Reduction in dislocation-dislocation interactions	X		
Line tension change	X		
Cross-slip rate change			X
Drag force exerted by atmosphere		X	

# Solute drag

- Using finite differences, solve for steady-state concentration and drag force
  - Considered both perfect and extended dislocations



Low velocity regime ( $v \ll v_c$ )

$$F_s \approx B_s(\theta)v$$

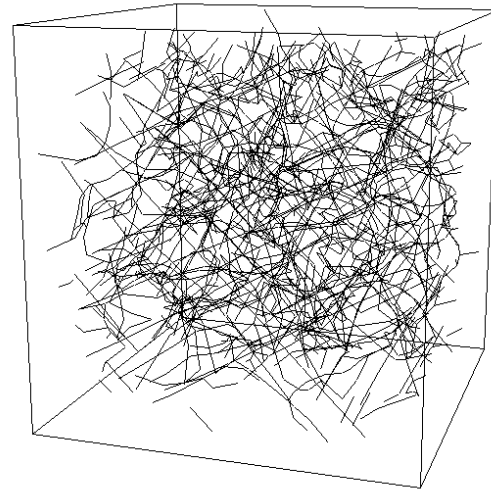
Character Angle



Hydrogen Mobility Law

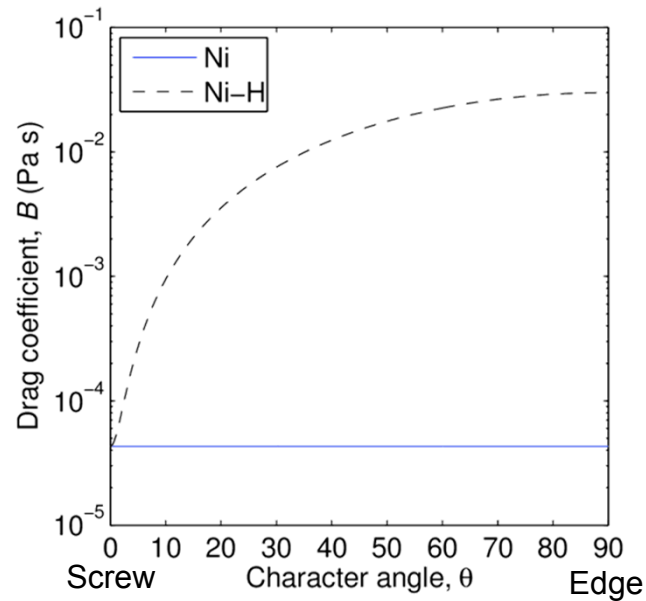
$$(B_s(\theta) + B_{ph})\mathbf{v}_i = \sum f_i$$

## **DD Simulations with H-Effects**

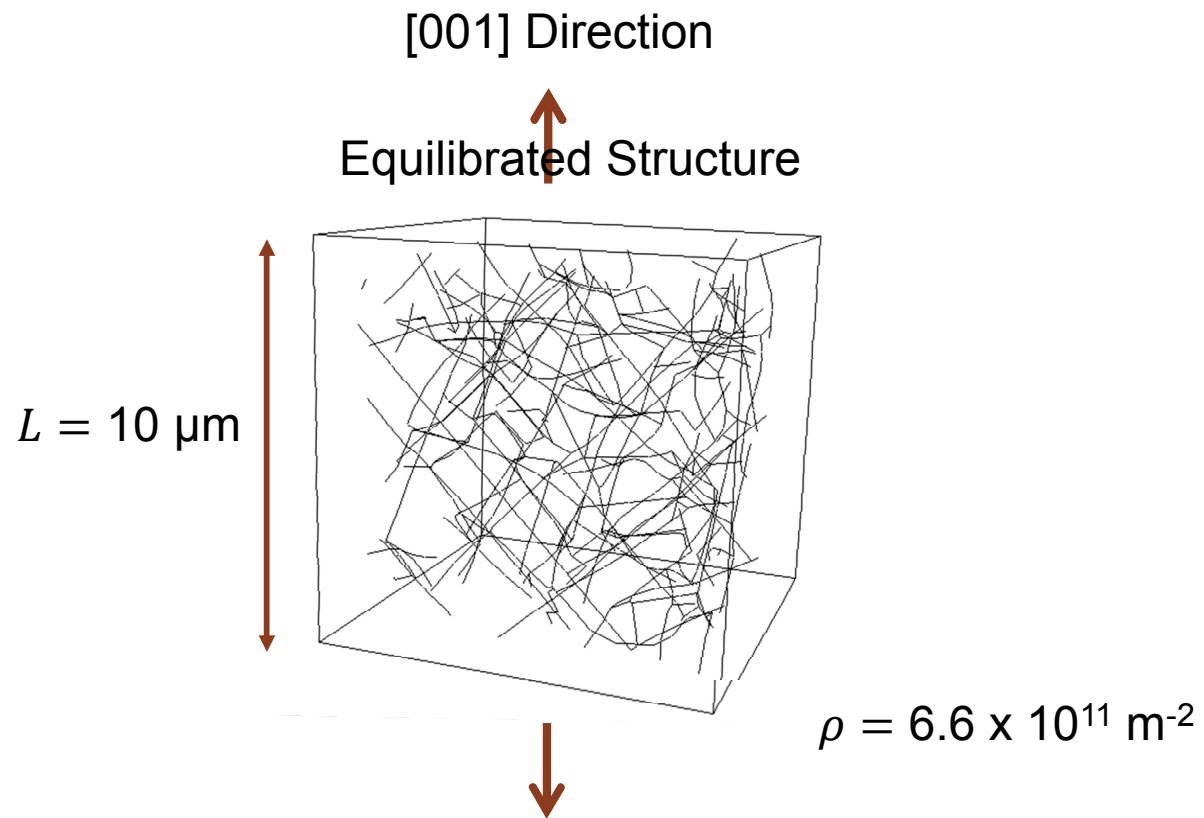


## Case: Ni-H at 800 K with 1 at. % H

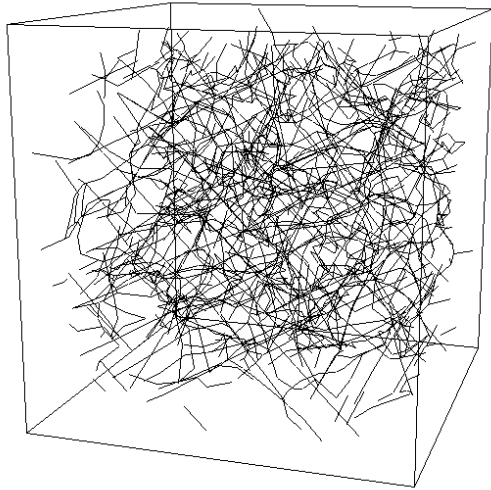
H-Effect on Force Calculation	Value
Edge-Edge elastic interaction change	-3.4%
Edge line energy change	-4.8%



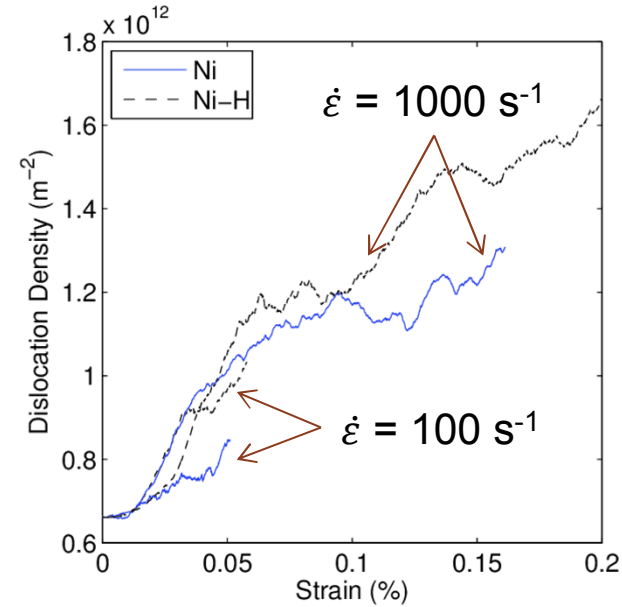
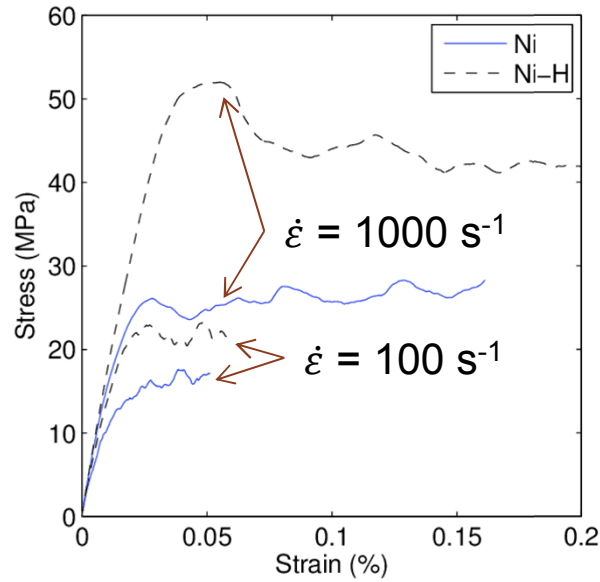
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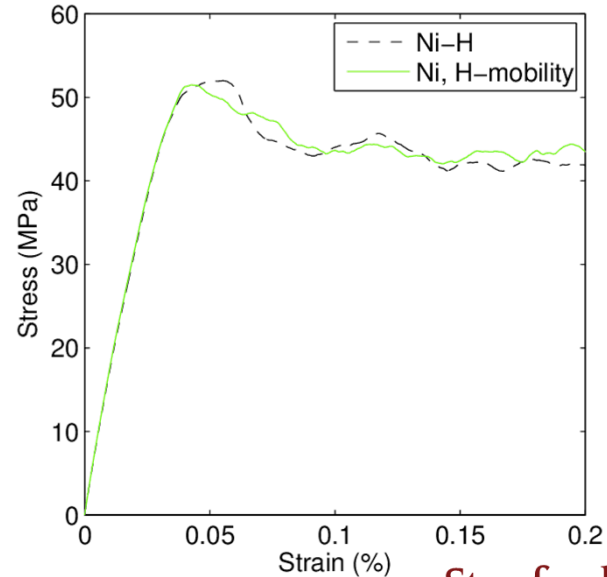
# Ni-H Results



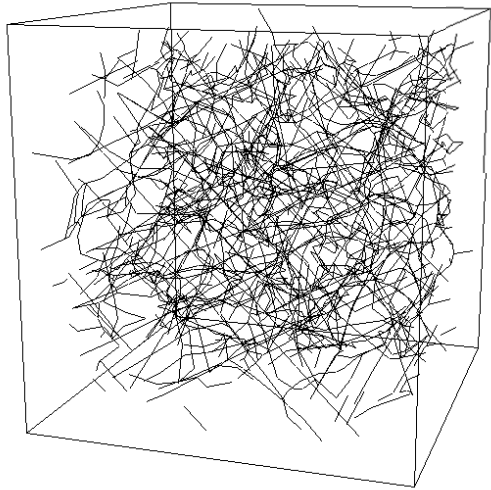
Ni-H at 0.2% strain



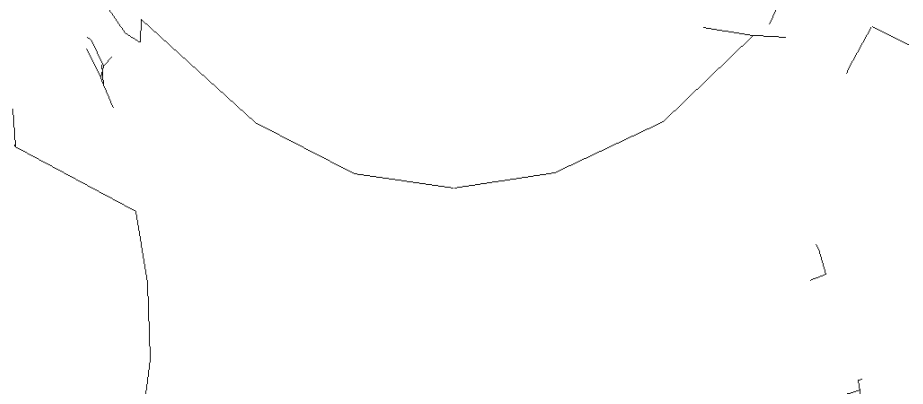
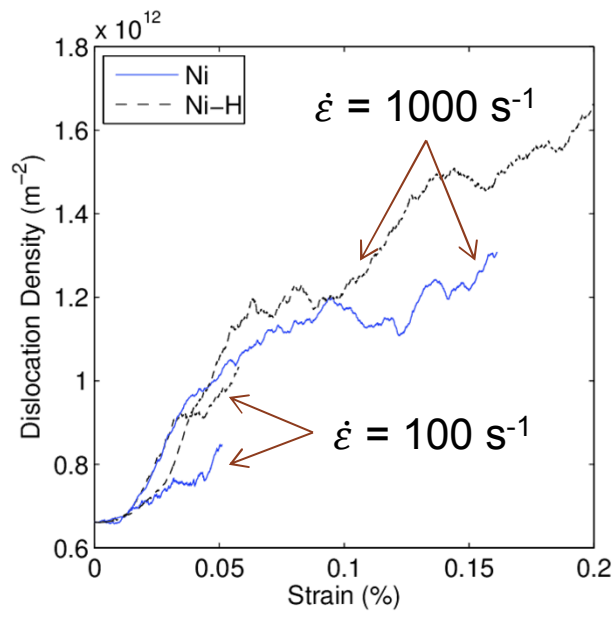
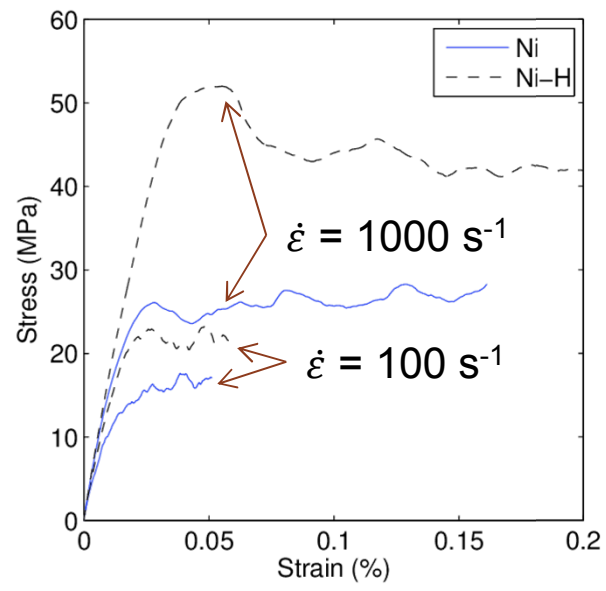
- Behavior dominated by drag force change



# Ni-H Results

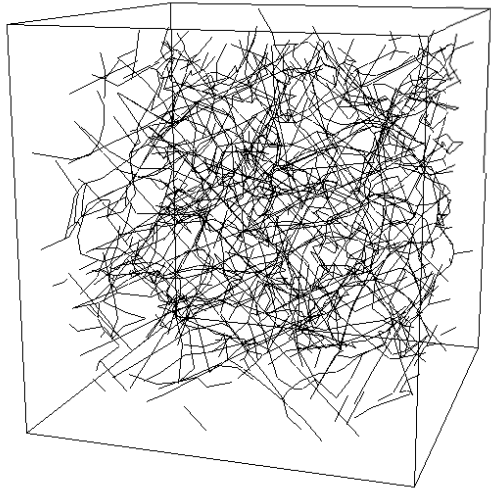


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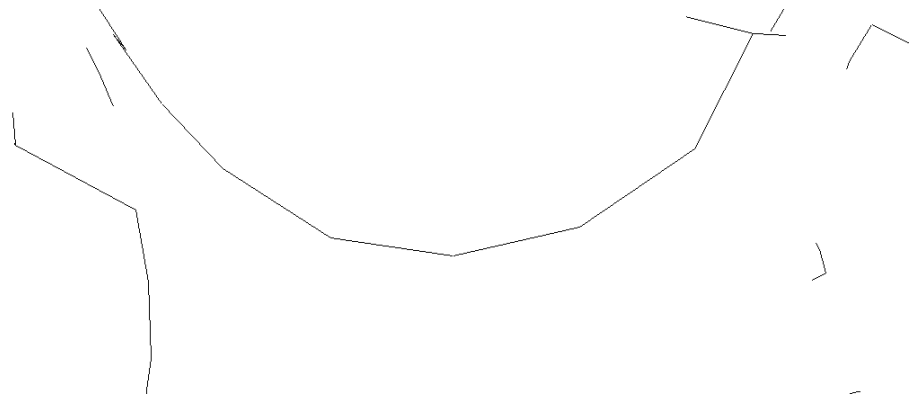
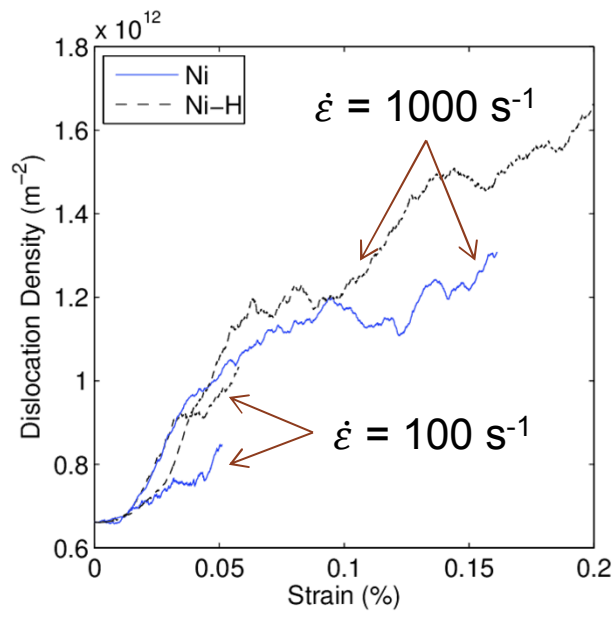
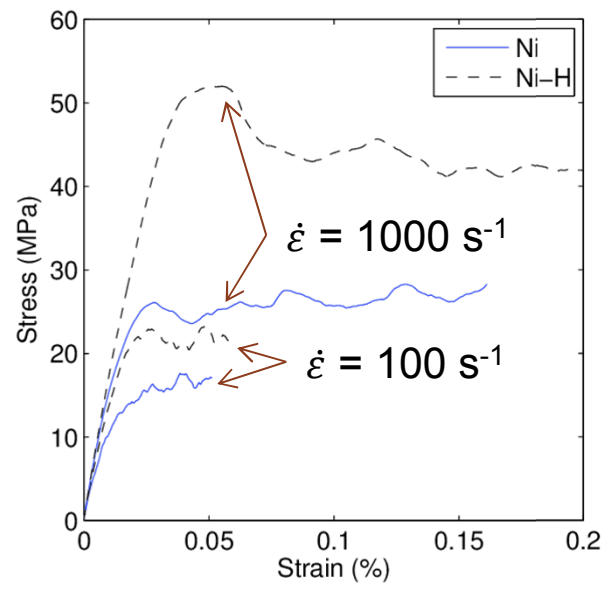


Ni-H

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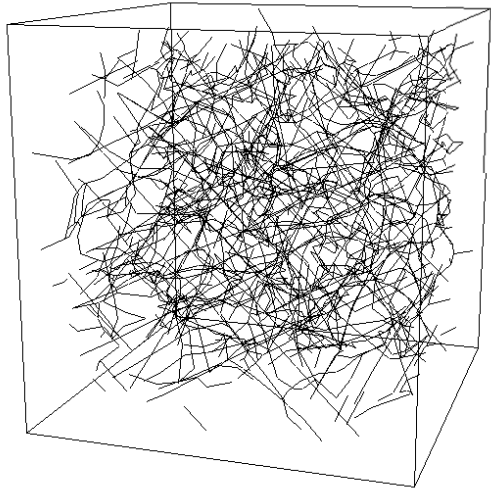


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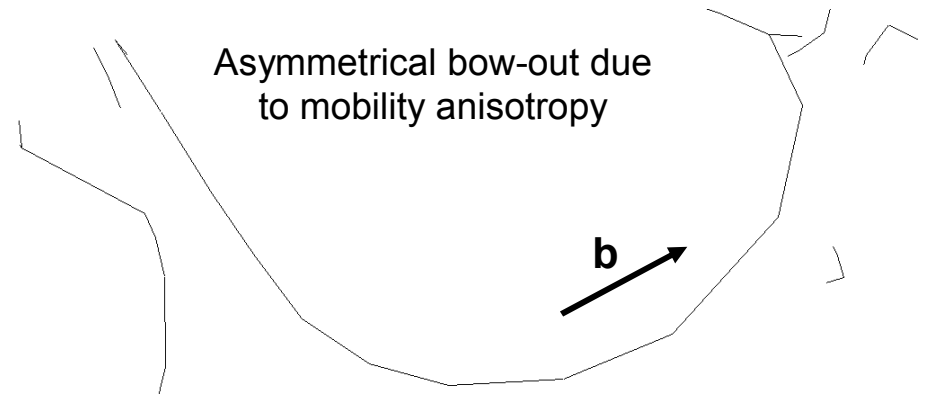
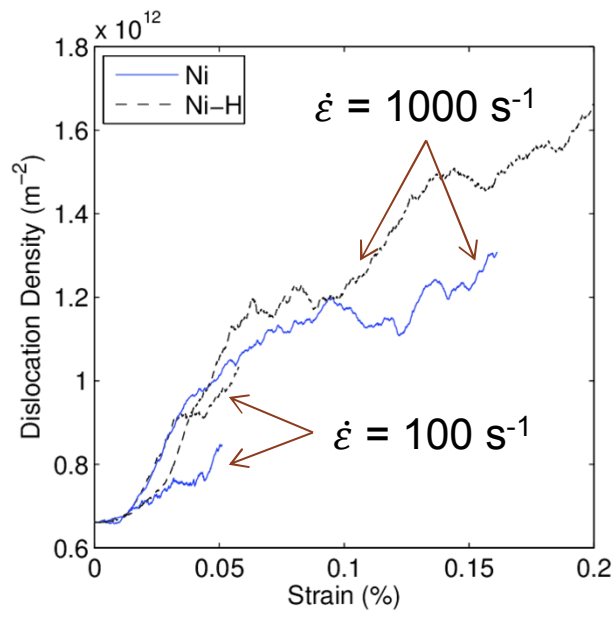
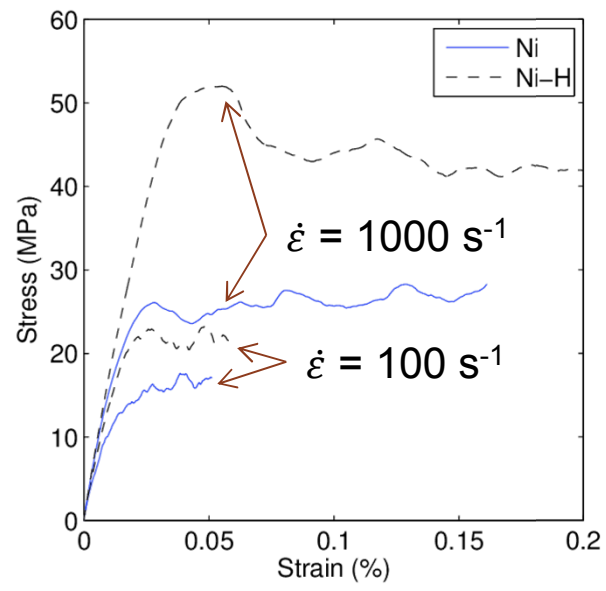


Ni-H

# Ni-H Results



Ni-H at 0.2% strain



Ni-H

## Conclusions

- Including hydrogen (solutes) in DD simulations requires consideration of multiple effects
- Classical continuum model useful approach for assessing effects
- Future work: Consider different diffusion regimes
  - › Fast diffusion vs. dynamic strain aging vs. slow diffusion
- R. B. Sills and W. Cai, *Solute drag on perfect and extended dislocations*, In-Preparation for JMPS.